

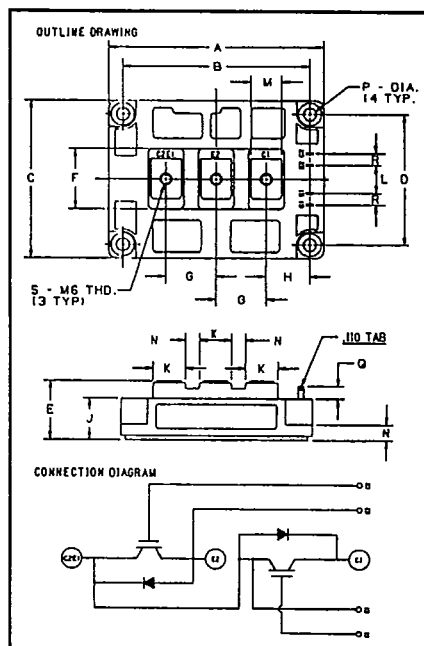


Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272
 Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

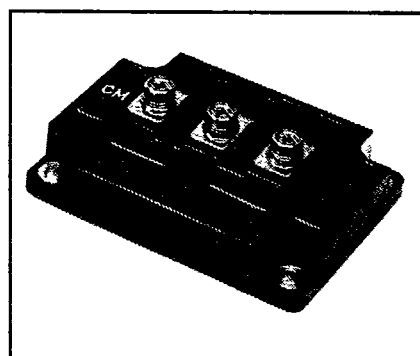
ID121215 - T-39-31

Dual IGBTMOD™ Power Module

150 Amperes/1200 Volts



ID121215
Outline Drawing



ID121215
Dual IGBTMOD™ Power Module
150 Amperes/1200 Volts

Description

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half bridge configuration, with each transistor having a reverse-connected super-fast recovery free wheel diode. All components and interconnects are isolated from the heat sinking base-plate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (150ns) Free Wheel Diode
- ☐ High Frequency Operation (15-20kHz)
- ☐ Isolated Base Plate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information

Example: Select the complete eight digit part module number you desire from the table below -i.e. ID121215 is a 1200V (V_{CES}), 150 Ampere Dual IGBTMOD™ Power Module.

Dimension	Inches	Millimeters
A	4.33	110.0
B	3.661±.010	93±0.25
C	3.15	80.0
D	2.441±.010	62.00±0.25
E	1.18 Max.	30.0 Max.
F	1.18	30.0
G	.98	25.0
H	.85	21.5
J	.83	21.2
K	.71	18.0
L	.59	15.0
M	.55	14.0
N	.28	7.0
P	.26 Dia.	Dia. 6.5
Q	.26	6.5
R	.24	6.0
S	M6 Metric	M6

Type	V_{CES} Volts (x100)	Current Rating Amperes (x10)
ID12	12	15



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Absolute Maximum Ratings, $T_J = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	ID121215	Units
Junction Temperature	T_J	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage	V_{GES}	± 20	Volts
Collector Current	I_C	150	Amperes
Peak Collector Current	I_{CM}	300*	Amperes
Diode Forward Current	I_{FM}	150	Amperes
Diode Forward Surge Current	I_{FM}	300*	Amperes
Power Dissipation	P_d	1100	Watts
Max. Mounting Torque M6 Terminal Screws	—	26	in.-lb.
Max. Mounting Torque M6 Mounting Screws	—	26	in.-lb.
Module Weight (Typical)	—	500	Grams
Visolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating.

Static Electrical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 15\text{mA}, V_{CE} = 10V$	3.0	4.0	6.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150A, V_{GE} = 15V$	—	3.5	5.0**	Volts
		$I_C = 150A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	—	3.5	**	Volts
Total Gate Charge	Q_G	$V_{CC} = 600V, I_C = 150A, V_{GS} = 15V$	—	1100	—	nC
Diode Forward Voltage	V_{FM}	$I_C = -150A, V_{GS} = 0V$	—	—	2.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible

Dynamic Electrical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{GE} = 0V, V_{CE} = 10V, f = 1\text{MHz}$	—	—	33000	pF
Output Capacitance	C_{oes}		—	—	8300	pF
Reverse Transfer Capacitance	C_{res}		—	—	830	pF
Resistive Load	Turn-on Delay Time	$V_{CC} = 600V, I_C = 150A, V_{GE1} = V_{GE2} = 15V, R_G = 8.3\Omega$	—	—	800	ns
	Rise Time		—	—	700	ns
	Turn-off Delay Time		—	—	800	ns
	Fall Time		—	—	1000	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 150A, di_E/dt = -300A/\mu\text{s}$	—	—	300	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 150A, di_E/dt = -300A/\mu\text{s}$	—	3.3	—	μC

Thermal and Mechanical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.11	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Free Wheel Diode	—	—	0.24	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Half Module	—	—	0.07	$^\circ\text{C/W}$



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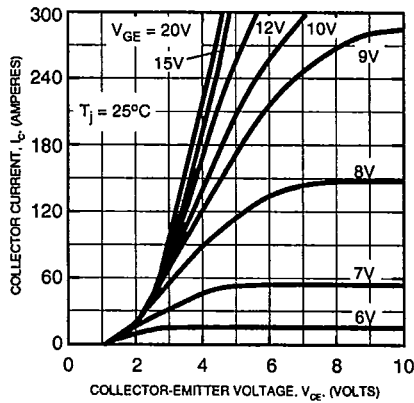
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ID121215

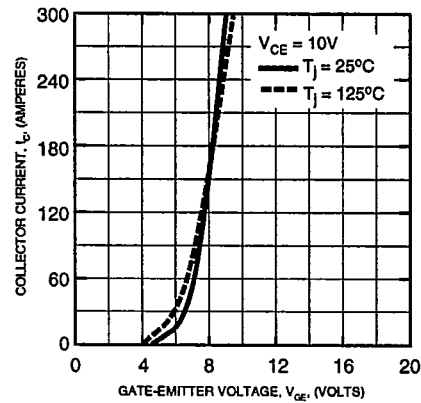
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150 Amperes/1200 Volts

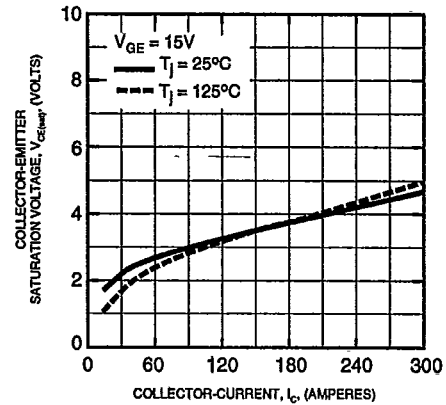
OUTPUT CHARACTERISTICS
(TYPICAL)



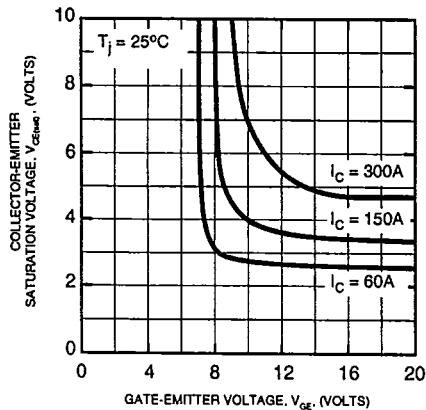
TRANSFER CHARACTERISTICS
(TYPICAL)



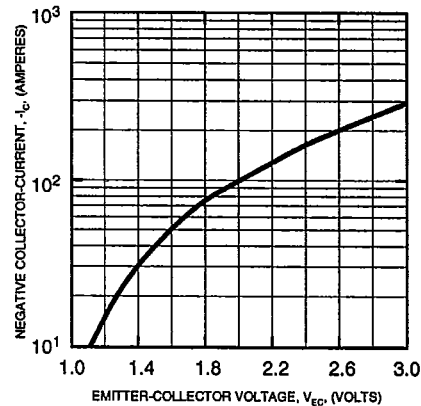
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



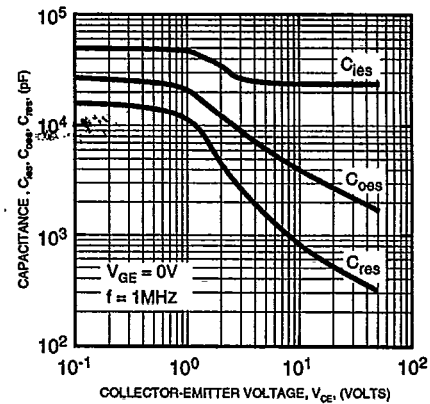
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



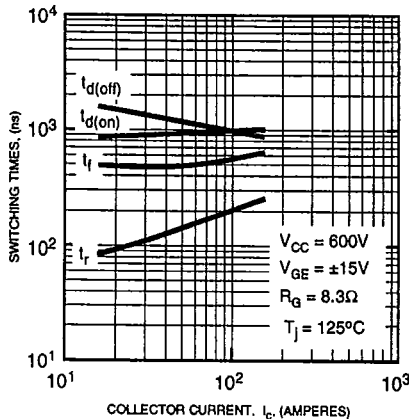
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



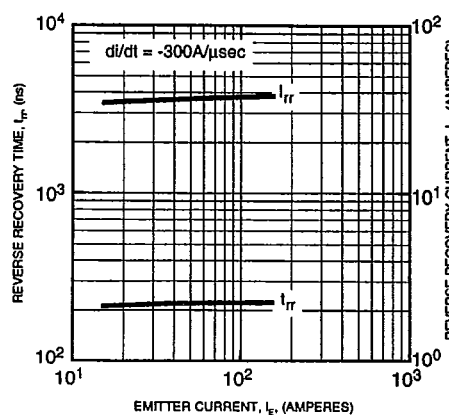
CAPACITANCE VS. V_{ce}
(TYPICAL)



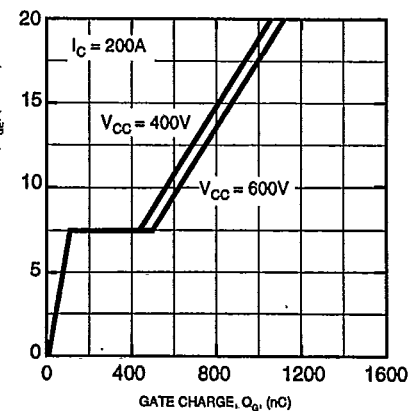
HALF BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, V_{ge}





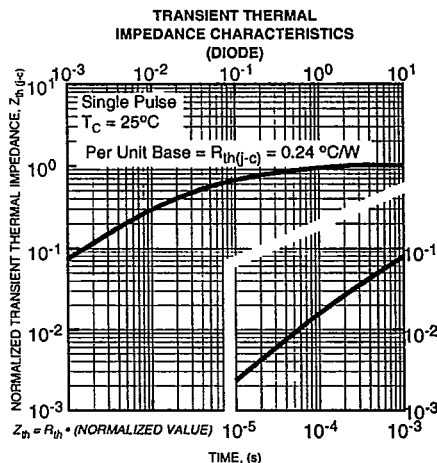
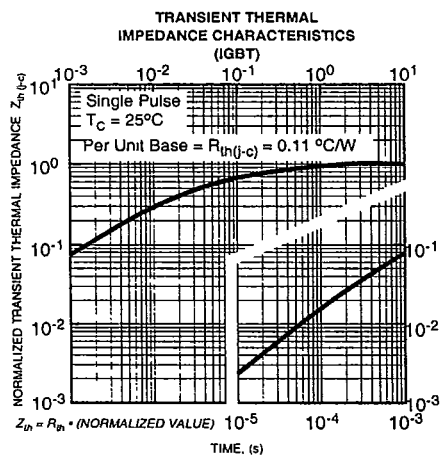
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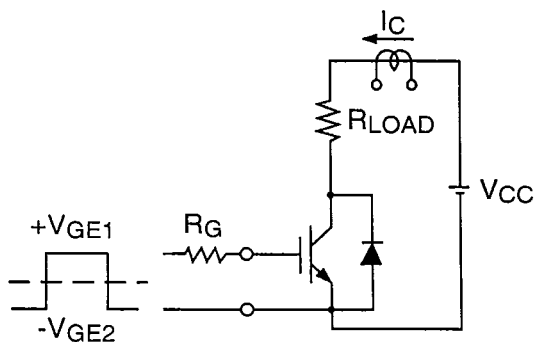
ID121215

Dual IGBTMOD™ Power Module

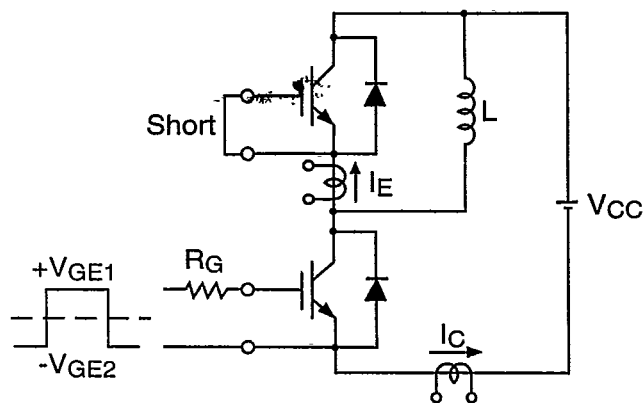
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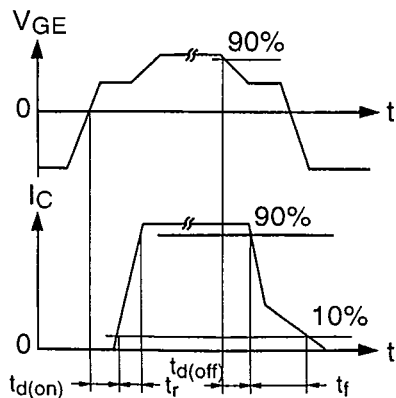
SWITCHING TIME TEST CIRCUITS & WAVEFORMS



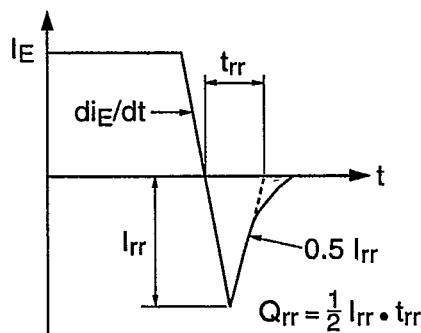
Resistance Load Switching Test Circuit



Half-Bridge Switching Test Circuit



Switching Time Test Waveforms



t_{rr} , Q_{rr} Waveforms